## 1. General description

PNP high power bipolar transistor in a power DPAK, TO-252 (SOT428C) Surface-Mounted Device (SMD) plastic package.

NPN complement: MJD41C-Q

### 2. Features and benefits

- · High thermal power dissipation capability
- · High energy efficiency due to less heat generation
- Electrically similar to popular MJD42 series
- · Low collector emitter saturation voltage
- Fast switching speeds
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Constant current drive backlighting application
- Motor drive
- Relay replacement

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-100	V
I <sub>C</sub>	collector current		-	-	-6	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-10	Α
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -4 V; $I_{C}$ = -0.3 A; pulsed; $t_{p}$ ≤ 200 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	30	-	-	
		$V_{CE}$ = -4 V; $I_{C}$ = -3 A; pulsed; $t_{p}$ ≤ 200 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	15	-	-	



### 100 V, 6 A PNP high power bipolar transistor

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	mb	
2	С	collector		Ę
3	Е	emitter		в -[^
mb	С	mounting base; connected to collector	DPAK (SOT428C)	C; mb aaa-029523

## 6. Ordering information

**Table 3. Ordering information** 

Type number	Package					
	Name	Description	Version			
MJD42C-Q		Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428C			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
MJD42C-Q	MJD42CA

# 8. Limiting values

#### Table 5. Limiting values

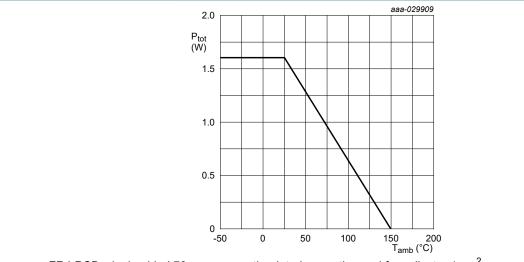
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base		-	-100	V
$V_{EBO}$	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-6	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-10	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C	[1]	-	15	W
		T <sub>amb</sub> ≤ 25 °C	[2]	-	1.6	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Total power dissipation junction to mounting base.

<sup>[2]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided 70 μm copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

#### 100 V, 6 A PNP high power bipolar transistor



FR4 PCB, single-sided 70 µm copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

Fig. 1. Power derating curves SOT428C

#### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	79	K/W
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	9	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided 70 µm copper, tin-plated mounting pad for collector 1 cm<sup>2</sup>.

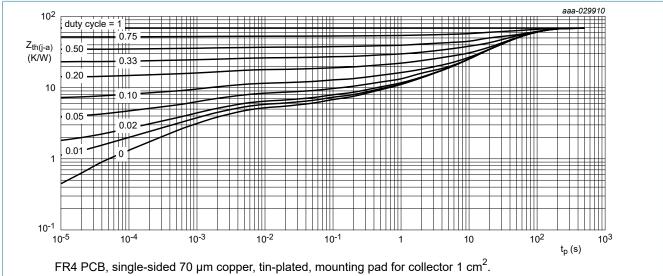


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 100 V, 6 A PNP high power bipolar transistor

## 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -80 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-1	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-1	μΑ
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -4 V; $I_{C}$ = -0.3 A; pulsed; $t_{p}$ ≤ 200 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	30	-	-	
		$V_{CE}$ = -4 V; $I_{C}$ = -3 A; pulsed; $t_{p}$ ≤ 200 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	15	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -6 A; $I_B$ = -600 mA; pulsed; $t_p$ ≤ 200 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.5	V
$V_{BE}$	base-emitter voltage	$V_{CE}$ = -4 V; $I_{C}$ = -6 A; pulsed; $t_{p}$ ≤ 200 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-2	V
h <sub>fe</sub>	small-signal current gain	$V_{CE}$ = -10 V; $I_{C}$ = -500 mA; f = 1 kHz; pulsed; $t_{p} \le 300$ µs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	20	-	-	
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -500 mA; f = 100 MHz; $T_{amb}$ = 25 °C	3	-	-	MHz

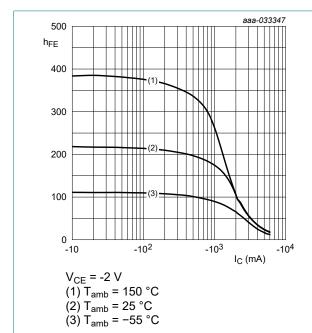


Fig. 3. DC current gain as a function of collector current; typical values

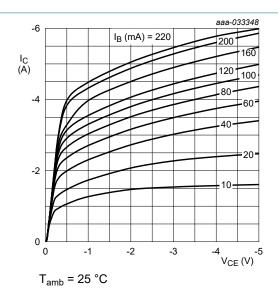
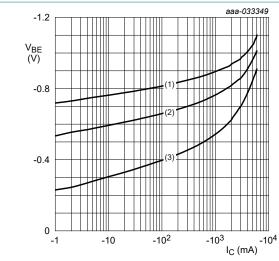


Fig. 4. Collector current as a function of collectoremitter voltage; typical values

-1.2

#### 100 V, 6 A PNP high power bipolar transistor

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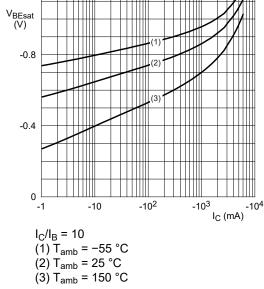


$$V_{CE} = -4 V$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

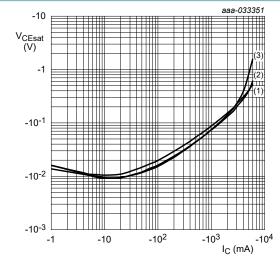
(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 5. Base-emitter voltage as a function of collector current; typical values



(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values



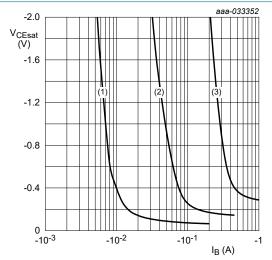
$$I_{\rm C}/I_{\rm B} = 10$$

$$(1) T_{amb} = 150 °$$

(1) 
$$T_{amb} = 150 \,^{\circ}C$$
  
(2)  $T_{amb} = 25 \,^{\circ}C$ 

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



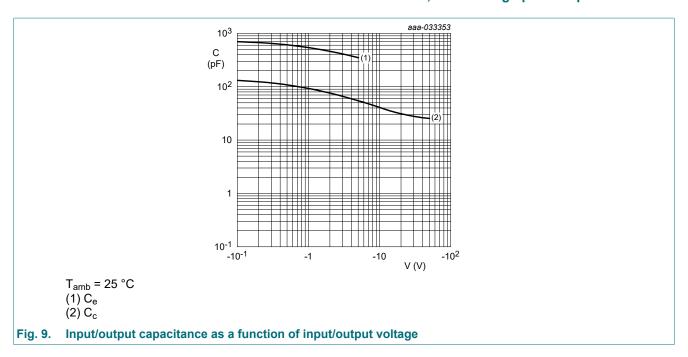
$$(1) I_C = -1 A$$

$$(2) I_C = -2.5 A$$

$$(3) I_C = -5 A$$

Fig. 8. Collector-emitter saturation region as a function of base current; typical values

#### 100 V, 6 A PNP high power bipolar transistor

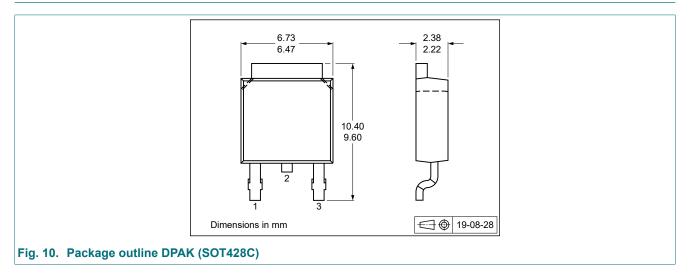


### 11. Test information

#### **Quality information**

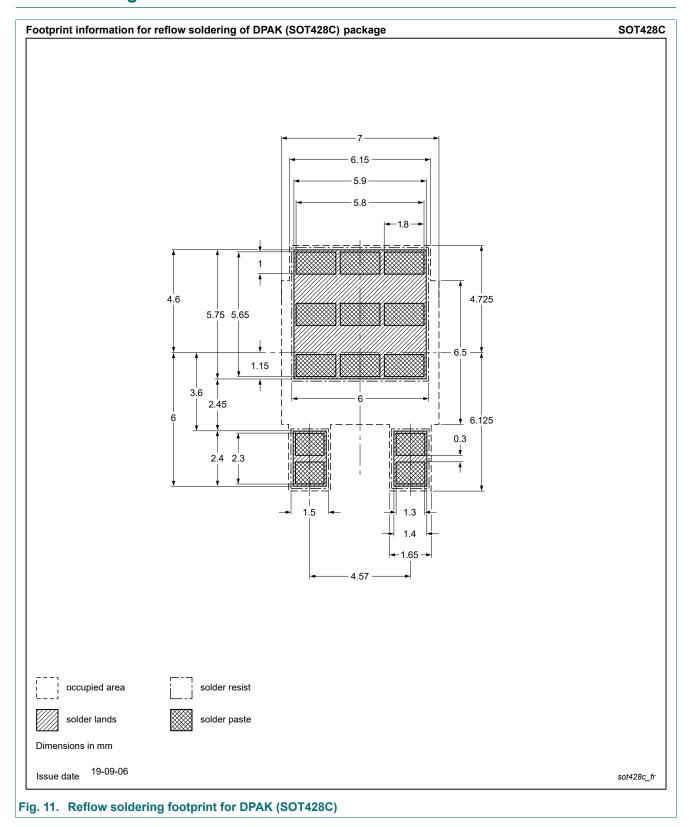
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

## 12. Package outline



100 V, 6 A PNP high power bipolar transistor

# 13. Soldering



### 100 V, 6 A PNP high power bipolar transistor

# 14. Revision history

#### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
MJD42C-Q v.2	20210608	Product data sheet	-	MJD42C-Q v.1				
Modifications:	Product status chang	Product status changed						
MJD42C-Q v.1	20210416	Objective data sheet	-	-				

## 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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#### 100 V, 6 A PNP high power bipolar transistor

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MJD42C-Q

### 100 V, 6 A PNP high power bipolar transistor

## **Contents**

1.	General description	. 1
2.	Features and benefits	. 1
3.	Applications	. 1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	. 2
8.	Limiting values	. 2
9.	Thermal characteristics	. 3
10	Characteristics	. 4
11.	Test information	6
12	Package outline	. 6
13	Soldering	. 7
	Revision history	
	Legal information	

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10 / 10

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